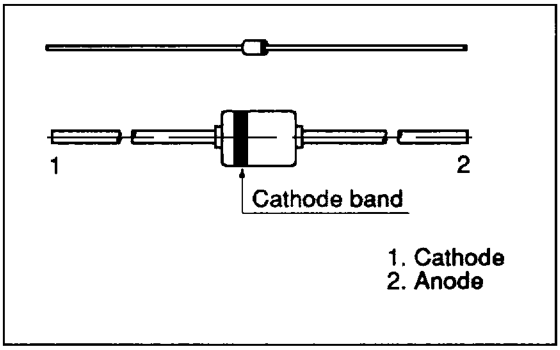
HSS104

Silicon Epitaxial Planar Diode for High Speed Switching

Features

- Short reverse recovery time and forward recovery time.
- Suitable for 5mm pitch high speed automatical insertion.
- Small glass package (MHD) enables easy mounting and high reliability.

Outline



Ordering Information

Type No.	Cathode band	Package Code
HSS104	Blue	MHD

Absolute Maximum Ratings (Ta = 25°C)

Item	Symbol	Value	Unit
Peak reverse voltage	V_{RM}	40	V
Reverse voltage	V_R	35	V
Peak forward current	I_{FM}	300	mA
Non Repetitive peak forward surge current	I_{FSM} *	0.4	A
Average forward current	I_o	110	mA
Power dissipation	P_d	300	mW
Junction temperature	T_j	175	°C
Storage temperature	T_{stg}	-65 to +175	°C

* Within 1s forward surge current

Electrical Characteristics (Ta = 25°C)

Item	Symbol	Min	Typ	Max	Unit	Test Condition
Forward voltage	V_F	—	—	1.2	V	$I_F = 100$ mA
Reverse current	I_R	—	—	0.5	μA	$V_R = 35$ V
Capacitance	C	—	—	3.0	pF	$V_R = 0.5$ V, f = 1 MHz
Reverse recovery time	t_{rr}	—	—	3.0	ns	I_F=10mA, V_R=6V, R_L=50Ω

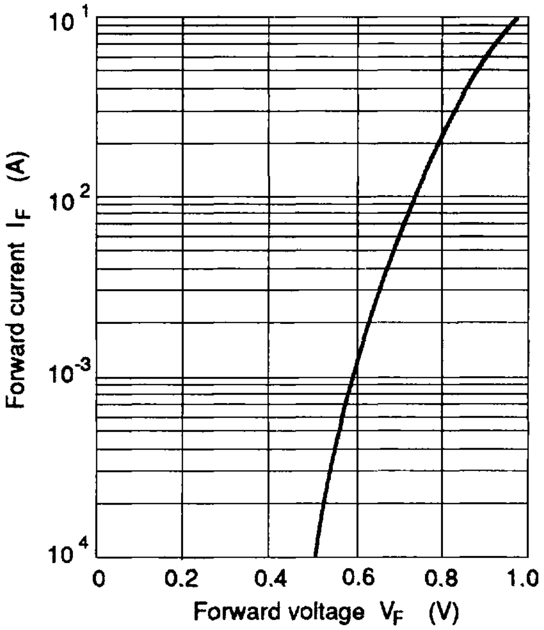


Fig.1 Forward current Vs. Forward voltage

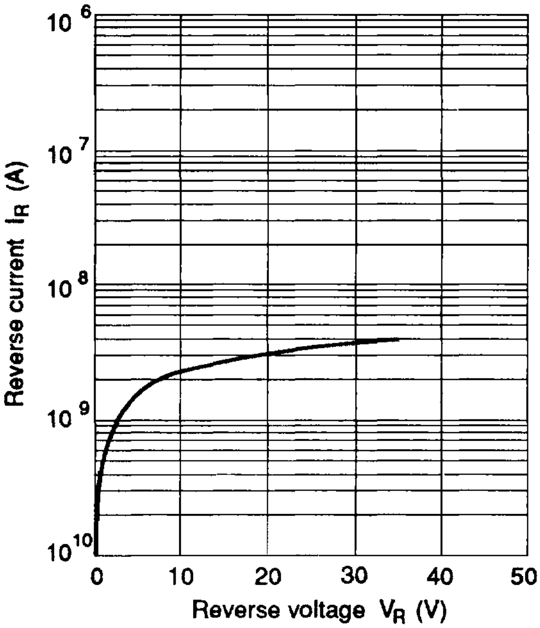


Fig.2 Reverse current Vs. Reverse voltage

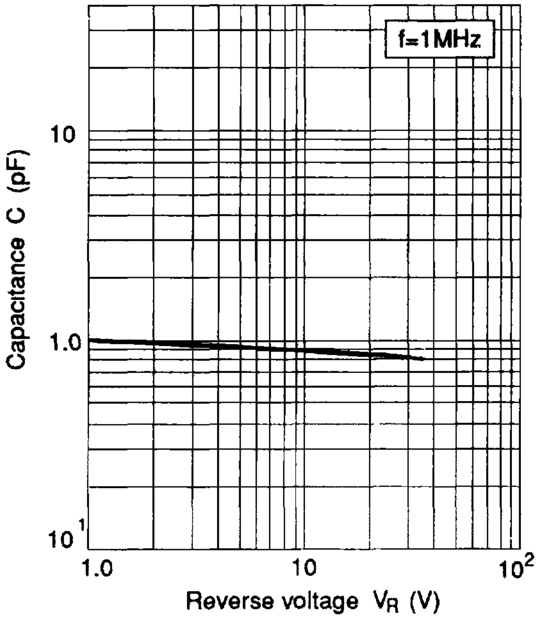


Fig.3 Capacitance Vs. Reverse voltage